PATENT COOPERATION TREATY



PCT

INTERNATIONAL PRELIMINARY EXAMINATION REPORT

(PCT Article 36 and Rule 70)

Applicant's or agent's file reference PF-3165	FOR FURTHER ACTION	ON See Notifi	cation of Transmittal of International Examination Report (Form PCT/IPEA/416)
International application No. PCT/JP2003/007676	International filing date (d 17 June 2003 (17	•	Priority date (day/month/year) 17 June 2002 (17.06.2002)
International Patent Classification (IPC) or n H01L 29/47, 29/872, 21/338, 29		С	
Applicant	NEC CORPOR	ATION	
and is transmitted to the applicant at 2. This REPORT consists of a total of This report is also accompan amended and are the basis for 70.16 and Section 607 of the These annexes consist of a total 3. This report contains indications related at the Basis of the report II Priority	5 sheets, inc. 5 sheets, inc. ided by ANNEXES, i.e., sheets of this report and/or sheets of Administrative Instructions of the following items: of opinion with regard to no	luding this cover sets of the descriptiontaining rectifics under the PCT).	sheet. ion, claims and/or drawings which have been ations made before this Authority (see Rule
Reasoned statemen	at under Article 35(2) with renations supporting such state	egard to novelty, i	nventive step or industrial applicability;
VI Certain documents	cited		į
VII Certain defects in t	he international application		
VIII Certain observation	ns on the international applic	cation	
Date of submission of the demand		ate of completion	of this report
17 June 2003 (17.06.		_	March 2004 (03.03.2004)
Name and mailing address of the IPEA/JP	A	uthorized officer	
Facsimile No.	т	elephone No.	

Form PCT/IPEA/409 (cover sheet) (July 1998)

Translation

INTERNATIONAL PRELIMINARY EXAMINATION REPORT

International application No.

PCT/JP2003/007676

Vith regard	to the elements of the international application:*	
the in	aternational application as originally filed	
=	escription:	
	1-32	, as originally filed
page:	S	, filed with the demand
page	, filed with	the letter of
the c	elaims:	, as originally filed
page	, as am	ended (together with any statement under Article 19
page		
page	36-89 filed with	the letter of12 November 2003 (12.11.2003)
page	es,	
the d	drawings:	, as originally filed
pag		, filed with the demand
pag		the letter of
pag		Title letter or
The se	equence listing part of the description:	
Dag		, as originally filed
pag		
pag	nieu wii	h the letter of
th or	the language of publication of the international application (under Rule language of the translation furnished for the purposes of internation 755.3). The gard to any nucleotide and/or amino acid sequence disclosed hary examination was carried out on the basis of the sequence listing: contained in the international application in written form. The statement that the subsequently in written form. The statement that the subsequently furnished written sequence international application as filed has been furnished. The statement that the information recorded in computer readable been furnished.	d in the international application, the internation form.
5.	the description, pages the claims, Nos	esponse to an invitation under Article 14 are referred t since they do not contain amendments (Rule 76)

International application No.
PCT/JP 03/07676

v.	Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability citations and explanations supporting such statement

Claims	36-89	YES
Claims		NO
Claims	36-89	YES
Claims		NO
Claims	36-89	YES
		NO
	Claims	Claims Claims Claims Claims Claims Claims 36-89

2. Citations and explanations

- Document 1: JP 2001-156081 A (Matsushita Electronics Industry Corporation), 8 June 2001
- Document 2: JP 2000-277724 A (President of Nagoya

 Institute of Technology et al.), 6 October

 2000
- Document 3: JP 11-354817 A (Furukawa Electric Co., Ltd.),
 24 December 1999
- Document 4: T. Egawa et al., Recessed gate AlGaN/GaN modulation-doped field-effect transistors on sapphire, Appl. Phys. Lett., 3 January 2000, Vol. 76, No. 1, pages 121 to 123
- Document 5: Takashi Egawa et al., Characteristics of a GaN

 Metal Semiconductor Field-Effect Transistor

 Grown on a Sapphire Substrate by Metalorganic

 Chemical Vapor Deposition, Jpn. J. Appl.

 Phys., April 1999, Vol. 38, Part 1, No. 4B,

 pages 2630 to 2633

Claims 36 to 89

The Schottky junction metal layer with a two-layer structure or a three-layer structure which constitutes the invention described in claims 36 to 89 is not disclosed in any of the documents cited in the international search report, and would not be obvious to a person skilled in

INTERNATIONAL PRELIMINARY EXAMINATION REPORT

International application No. PCT/JP 03/07676

the art.	

INTERNATIONAL PRELIMINARY EXAMINATION REPORT

International application No.

PCT/JP2003/007676

Certain documents cited						
Certain published documents	(Rule 70.10)					
Application No. Patent No.	Publicati (day/mon	on date th/year)	Filing date (day/month/year)	_	Priority date (valid clain (day/month/year)	1) —
JP 2003-209124	25 July 2003	(25.07.2003)	17 December 2001 (1	7.12.2001)	06 November 2001 (06.1	1.200
[EX]						
					-	
Non-written disclosures (Ru	ıle 70.9)			Dat	e of written disclosure	_
Kind of non-writter	n disclosure	Date of non-written disclosure (day/month/year)		referring to non-written disclosure (day/month/year)		
					•	